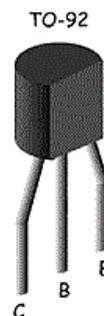




Kursy Elektroniki

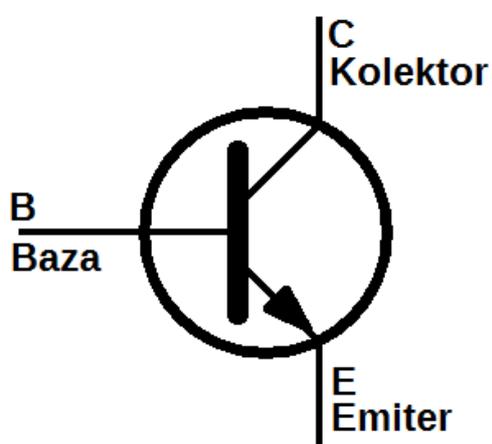
zajęcia 3



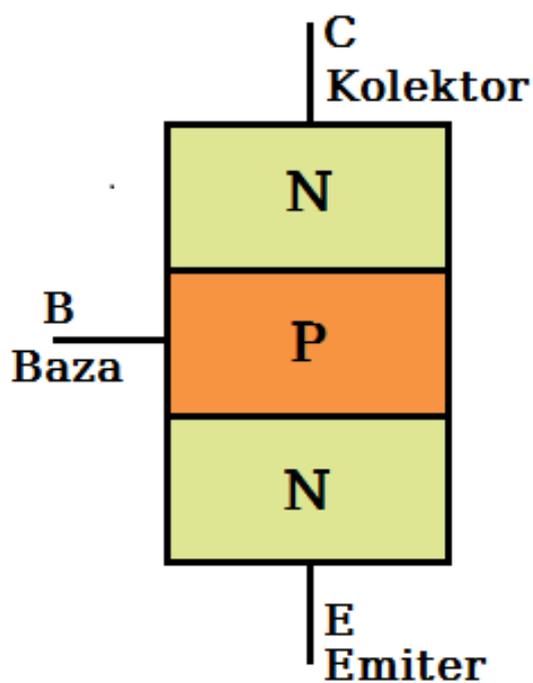
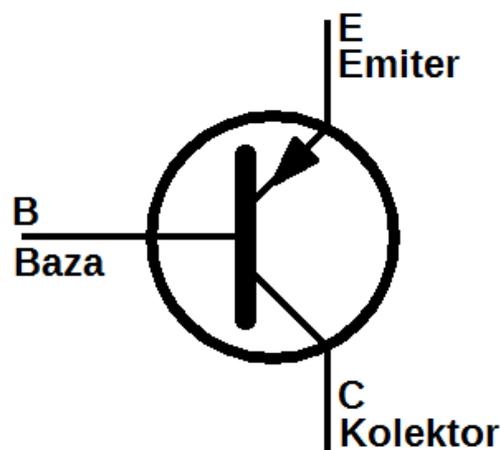
bc548
bc558

Tranzystory bipolarne:

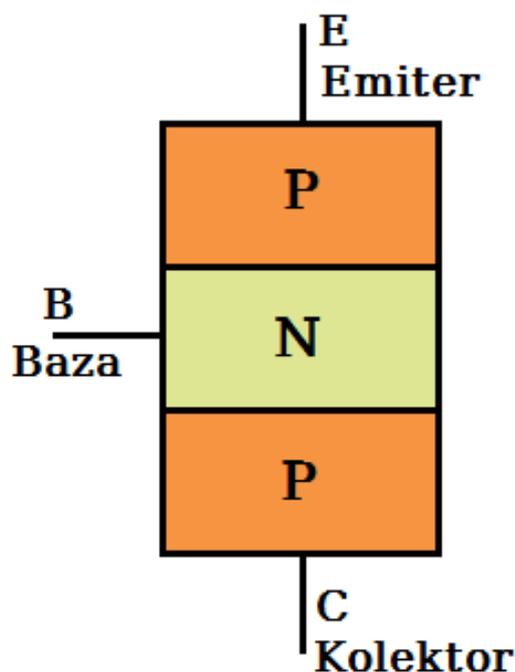
NPN



PNP

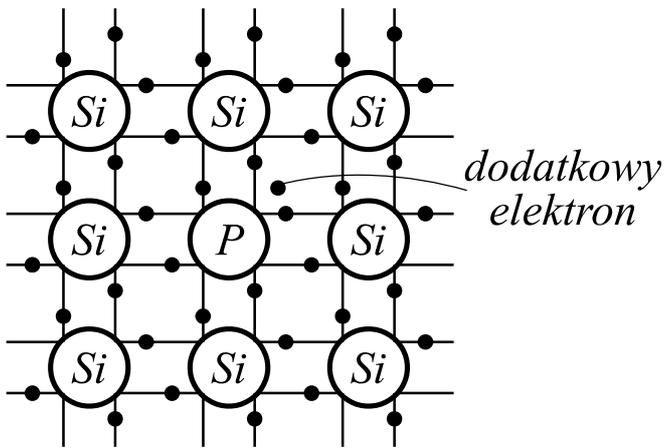


$$U_{BE (on)} \approx 0,6V$$

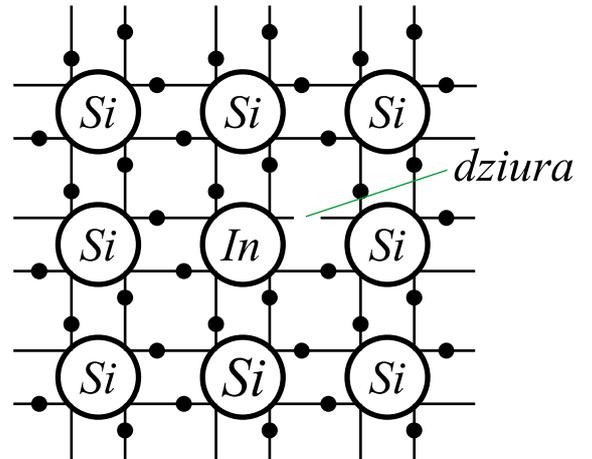


$$U_{BE (on)} \approx -0,6V$$

Półprzewodniki domieszkowane:

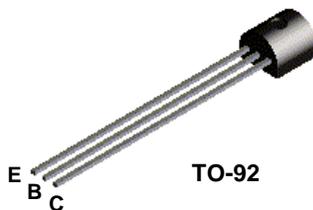


Typu N



Typu P

**BC548
BC548A
BC548B
BC548C**



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CES}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC548 / A / B / C	
P _D	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

NPN General Purpose Amplifier

(continued)

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	30		V
$V_{(BR)CES}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = +150 \text{ }^\circ\text{C}$		15 5.0	nA μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$			
		548	110	800	
		548A	110	220	
		548B	200	450	
		548C	420	800	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$		0.25 0.60	V V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$	0.58	0.70 0.77	V V

SMALL SIGNAL CHARACTERISTICS

h_{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	125	900	
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 200 \text{ } \mu\text{A},$ $R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $B_W = 200 \text{ Hz}$		10	dB

BC548 / BC548A / BC548B / BC548C